DESCRIPTION

~~METHOD FOR MANUFACTURING BONDED WAFER~~

TECHNICAL FIELD

[0001]

The present invention relates to a method of producing a bonded wafer by an ion implantation separation method, and particularly to a method of producing a bonded wafer by the ion implantation separation method by using a wafer reclaimed by performing a reclaiming process on a by-product wafer separated when a bonded wafer is produced by the ion implantation separation method.

BACKGROUND ART

[0002]

A method for producing SOI wafers by separating ions-implanted wafers after bonding, i.e., the ion implantation separation method (an art also referred to as the Smart Cut method (registered trademark)), has attracted attention as a method for producing SOI wafers, particularly SOI wafers each having a thin layer that enable the performance improvements of advanced integrated circuits.

[0003]

The ion implantation separation method is an art (See Patent Document 1) to form an SOI wafer in the following manner: an oxide film is formed on at least one of two silicon wafers, and gas ions, such as hydrogen ions or rare gas ions, are implanted from a front surface of one of the silicon wafers (a bond wafer) to form a layer of the implanted ions (also

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